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May 2024

FAN7384 Half-Bridge Gate-Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 250mA/500mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V_S Swing to -9.8V for Signal Propagation at V_{DD}=V_{BS}=15V
- Matched Propagation Delay Below 50ns
- Output In-Phase with Input Signal
- 3.3V and 5V Input Logic Compatible
- Built-in Shoot-Through Prevention Logic
- Built-in Common Mode dv/dt Noise Canceling Circ
- Built-in UVLO Functions for Both Channels
- Built-in Cycle-by-Cycle Shutdown Function
- Built-in Soft-Off Function
- Built-in Bi-Directional Fault Function
- Built-in Short-Circuit Protection unction

Applications

- Motor Inver Driver
- Normal >If-bridge a d Full-Bridge Driver
- f ... ing ndc ... ver Supply

Description

The FAN7384 is a monolithic house gate-drive IC designed for high voltage, high seed drong MOSFETs and IGBTs operating up to o00V.

Fairchild's high-vo'tage of cess and common mode noise canceling technique province stable operation of high-side drives under high and noise circumstances.

An advar, 'd', 'el-s', circuit all ws high-side gate driv an $u_P = \sqrt{s} = -9$ (v (typical) for $V_{BS} = 15$ V.

, a L '.O coolits prevent malfunction when $V_{\rm DD}$ and $V_{\rm B}$ are over than the specified threshold voltage.

Output drivers typically source/sities 250mA/500mA, espectively, which is stritable for half-bridge and full-bridge applications in motor trive systems.

14-SOP



Ordering Information

Part Number	Package	Operating Temperature Range	Packing Method
FAN7384MX ⁽¹⁾	14-Lead, Small Outline Integrated Circuit (SOIC), Non-JEDEC, .150 Inch Narrow Body, 225SOP	-40°C to +125°C	Tape & Reel

Note:

1. The device passed wave soldering test by JESD22A-111.

Typical Application Diagrams

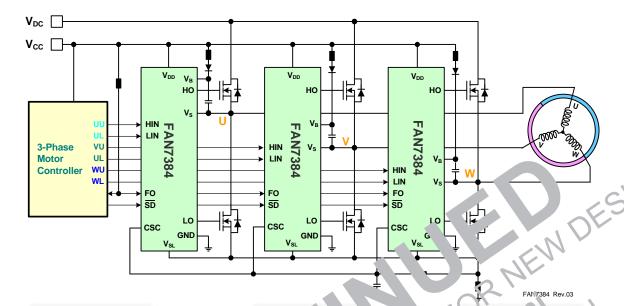


Figure 1. 3-Phar lotor L ve . plication

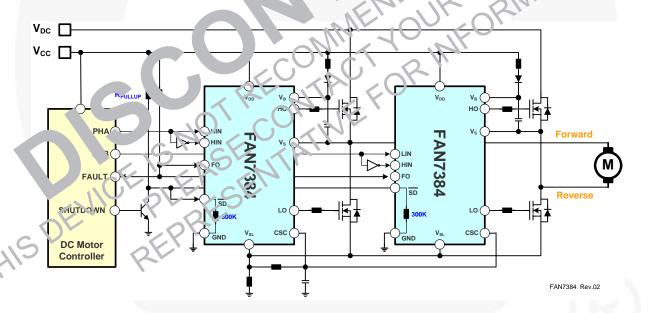


Figure 2. DC Motor Drive Application

Internal Block Diagram

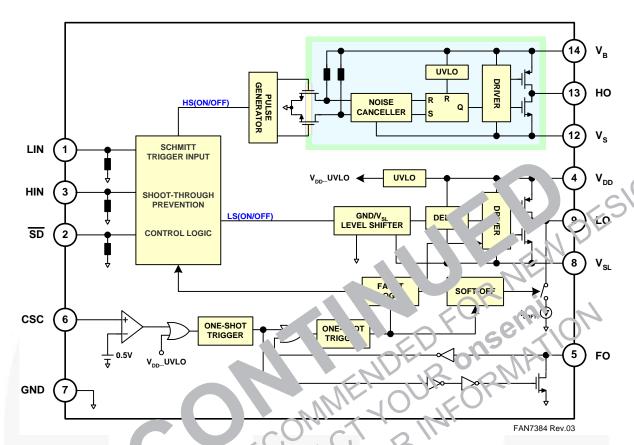


Figure 3. Functions! Block Mayram

Pin Configuration

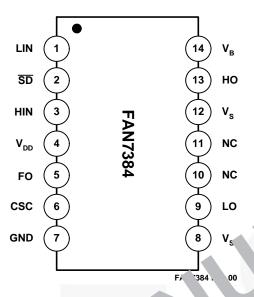


Figure 4. Pin Configuration

Pin Definitions

		FO (5) 1 (10) NC
		CSC 6 9 LO
		CSC 6 9 LO GND 7 8 V _s F/ '384' 00
		FA 384 : 00
		Figure 4. Pin Configuration (Table W) Description
Pin Definition	ns	IDED ONSUATION
Pin #	Name	Description
1	LIN	Los In, it for low-rice gate driver
2	C.	Shu own control input with active low
3	HIN	Jic Input for high-side gate driver
4	OD'	Lov-sice power supply voltage
5	Fu	Si-direction fault pin with open drain
6	CSC	Short-circuit current detection input
	GND	Ground
8	V _{SL}	Low-side supply offset voltage
	LO	Low side gate driver output
10	NC	Not connection
01	NC	Not connection
12	Ve	High-side floating supply offset voltage
13	НО	High-side gate driver output
14	V_{B}	High-side floating supply voltage

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
V _S	High-side offset voltage V _S	V _B -25	V _B +0.3	V
V _B	High-side floating supply voltage V _B	-0.3	625	V
V _{HO}	High-side floating output voltage	V _S -0.3	V _B +0.3	V
V _{DD}	Low-side and logic-fixed supply voltage	-0.3	25	V
V _{IN}	Logic input voltage (HIN, LIN, SD)	-0.3	V _D	V
V _{CSC}	Current sense input voltage	-0.3	V _L +0.3	V
V _{FO}	Fault output voltage	-0.3	V _{DD} 3	()
dV _S /dt	Allowable offset voltage slew rate		50	Vins
P _D ⁽²⁾⁽³⁾⁽⁴⁾	Power dissipation		1.0	W
θ_{JA}	Thermal resistance, junction-to-ambient		110	°C/W
T _J	Junction temperature		+150	°C
T _S	Storage temperature	-55	+150	°C

Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 s ss epo. material).
- 3. Refer to the following standards:
 - JESD51-2: Integral circuits ther and immigration vection JESD51-3: Low effective there all conductivity test board for leaded surface mount packages
- 4. Do not exceed PD und cil mstar s.

Recomme ued Oh rating Conditions

The Recommendations of the conditions for actual device operation. Recommended operating of ditions of specified to ensure optimal performance to the datasheet specifications. Fairchild does not make the specification of designing to Absolute Maximum Ratings.

3ymi J	Parameter	Condition	Min.	Max.	Unit
√B	High-side floating supply voltage	- 1	V _S +13	V _S +20	V
V's	High-side floating supply offset voltage		6-V _{DD}	600	V
V _D	Supply vo.tage		13	20	V
V _{HO}	High-vice output voltage		Vs	V_B	V
V_{LO}	Low-side output voltage		GND	V_{DD}	V
V _{IN}	Logic input voltage (HIN, LIN, SD)		GND	V_{DD}	V
V_{FO}	Fault output voltage		-0.3	V _{DD} +0.3	V
T _A	Ambient temperature		-40	+125	°C

Electrical Characteristics

 V_{BIAS} (V_{DD} , V_{BS}) = 15.0V, T_A = 25°C, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to GND. The V_O and I_O parameters are referenced to V_S and GND and are applicable to the respective outputs HO and LO.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
LOW SIDE	E POWER SUPPLY SECTION					
I_{QDD}	Quiescent V _{DD} supply current	V _{LIN} =0V or 5V		600	800	μΑ
I _{PDD}	Operating V _{DD} supply current	f _{LIN} =20kHz, rms value		950	1300	μΑ
V _{DDUV+}	V _{DD} supply under-voltage positive going threshold	V _{DD} =Sweep	10.9	11.9	12.9	٧
V _{DDUV-}	V _{DD} supply under-voltage negative going threshold	V _{DD} =Sweep	10.4	4	12.4	٧
V _{DDHYS}	V _{DD} supply under-voltage lockout hysteresis	V _{DD} =Sweep		0.5		V
BOOTSTF	RAPPED POWER SUPPLY SECTION				\overline{O}	
V _{BSUV+}	V _{BS} supply under-voltage positive going threshold	V _{BS} =Sweep	10.6	11.5	12.4	V
V _{BSUV} -	V _{BS} supply under-voltage negative going threshold	V _{BS} =Swe	10.1	11.0	11.9	٧
V _{BSHYS}	V _{BS} supply under-voltage lockout hysteresis	S=Sw()	SO	0.5	O	V
I _{LK}	Offset supply leakage current	V _B = ==600V	1	0/	10	μА
I_{QBS}	Quiescent V _{BS} supply current	V _{HIN} =UV or 5V	ON	50	90	μΑ
I_{PBS}	Operating V _{BS} supply f ren.	1HIN=?0,44.7,1ms vaide		400	600	μΑ
GATE DR	IVER OUTPUT SECTI N	All Aller				
V _{OH}	High-level or out voltag V- J-VO	ان=0m/، (No Load)			100	mV
V_{OL}	Low-level or ut volt e, Vo	Ic=Cn.A (No Lcad)			100	mV
I _{O+}	Or out HIGH & cuit rulse current	$V_0=0V$, $V_{IN}=5V$ with PW<10 μ s	200	250		mA
l _{O-}	Output LOV short-circuit puised current	V_{Q} -1 ξ V, V_{IN} =0V with PW<10 μ s	420	500		mA
Vs	ר wa. negative V _S pin voltage for IN sig. ! propagation to H _O			-9.8	-7.0	V
VS. SNF	V _{SL} -GND/GND-V _{S _} voltage endurability		-7.0		7.0	V
SHU DO	WN CONTROL SECTION (SD)					
SD+	Shutdown "1" input vol age				1.2	V
SD-	Shutdown "0" input voitage		2.5			V
LOGIC IN	PUT SECTION (YAN, LIN)				•	
V _{IH}	Logic "1" input voltage		2.5			V
V _{IL}	Logic "0" input voltage				1.2	V
V _{INHYS}	Logic input hysteresis voltage			0.5		V
I _{IN+}	Logic "1" input bias current	V _{IN} =5V	10	15	20	μΑ
I _{IN-}	Logic "0" input bias current	V _{IN} =0V			2.0	μА

Electrical Characteristics (Continued)

 V_{BIAS} (V_{DD} , V_{BS}) = 15.0V, T_A = 25°C, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to GND. The V_O and I_O parameters are referenced to GND and V_S is applicable to HO and LO.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
SHORT-C	IRCUIT PROTECTION			I		
V _{CSCREF}	Short-circuit detector reference voltage		0.47	0.50	0.53	V
I _{CSCIN}	Short-circuit input current	V _{CSCIN} =1V, R _{CSCIN} =100KΩ	5	10	15	μΑ
I _{SOFT}	Soft turn-off source current	V _{DD} =15V	5	10	15	mA
-V _{CSC}	Negative CSC pin immunity ⁽⁵⁾	Voltage on CSC pin up to -12V, Time<2 μ s			-20	V
FAULT DE	ETECTION SECTION					
V _{FINH}	Fault input high level voltage		2.5			V
V_{FINL}	Fault input low level voltage				1.2	V
V _{FINHYS}	Fault input hysteresis voltage ⁽⁵⁾			0.5		V
V _{FOH}	Fault output high level voltage	V _{CSC} =0V, R _{PULL} γ=4 ·KΩ	4.7			V
V_{FOL}	Fault output low level voltage	V _{CSC} =1V, I _r =2m _l		7.	0.8	V
t _{FO}	Fault output pulse width	V _{CSC'N} V		60	100	μs

Note:

5. These parameters guaranteed by design.

Dynamic Electrical Char .cte. tics

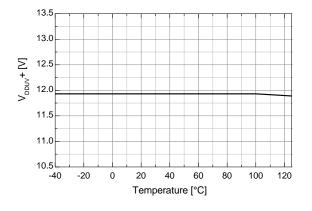
 $T_A=25^{\circ}C$, V_{BIAS} (V_{DD} , V_{BS}) – 15.0 $V_S=C$ D, C_{Locu} – 1000pF unless otherwice specified.

Symbol	Parametei	Conditions	Min.	Тур.	Max.	Unit
t _{on}	Tur un prop. ation elay	V _S =0V		180	260	ns
t _{off}	Tu. agation delay	V _S =0V or 500V ⁽⁵⁾		170	240	ns
	rn-c ri time	717		50	100	ns
t _f	Tu off fall time		<i>f</i> .	30	80	ns
T	Delay n atching				50	ns
D	Dead-tirne		80	120	170	ns
t _{UVFL1}	Under-voltage filtering fine (5)			16		μs
tcsc=i∄	CSC pin filtering time (5)			300		ns
†CSCFO	Time from C3C triggering to FO ⁽⁵⁾			350		ns
tcsclo	Time from CSC triggering to low-side gate output $^{(5)}$	From V _{CSC} =1V to starting gate turn-off		600	/	ns
t _{SDFO}	Shutdown to FO propagation delay ⁽⁵⁾			60		ns
t _{SDOFF}	Shutdown to HIGH/LOW-side gate off ⁽⁵⁾			100		ns

Note:

5. These parameters guaranteed by design.

Typical Characteristics



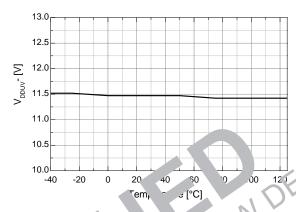
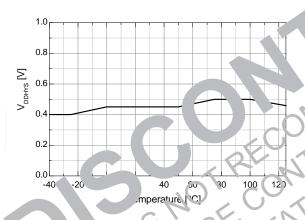
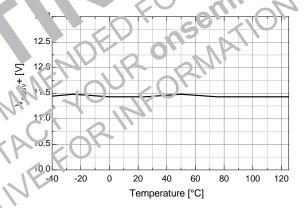


Figure 5. V_{DD} UVLO (+) vs. Temperature

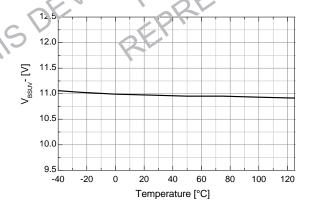
Fi vre V_{DD} /LO (-) vs. 1 emperature





rure V_{DD} UVLO Hysteres s. s. Temperature

Figure 8. V_{BS} UVLO (+) vs. Temperature



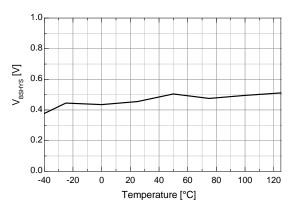
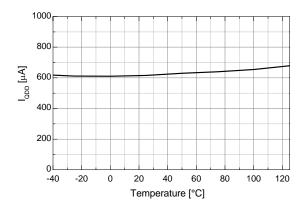


Figure 9. V_{BS} UVLO (-) vs. Temperature

Figure 10. V_{BS} UVLO Hysteresis vs. Temperature



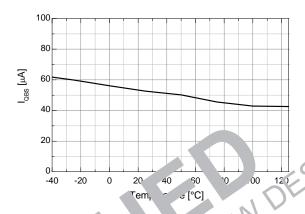
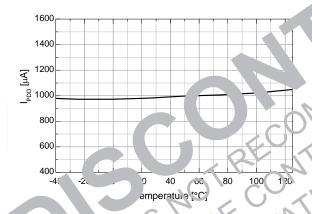
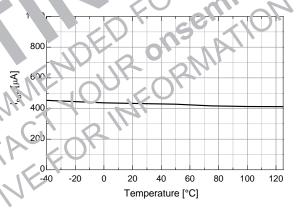


Figure 11. V_{DD} Quiescent Current vs. Temperature

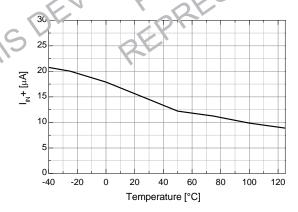
Figure V_L Quie: ent Current vs. Temperature

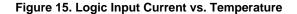




F. ire 1 V_{DD} Operating Current vs. Temperature

Figure 14. V_{BS} Operating Current vs. Temperature





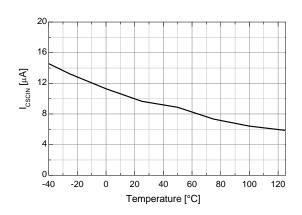
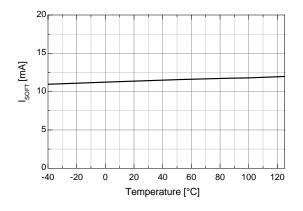


Figure 16. I_{CSCIN} vs. Temperature



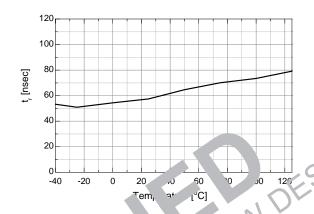
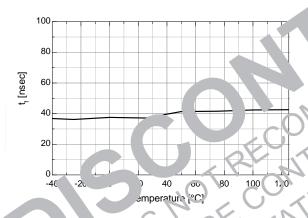
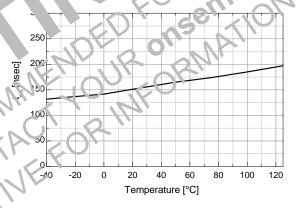


Figure 17. I_{SOFT} vs. Temperature

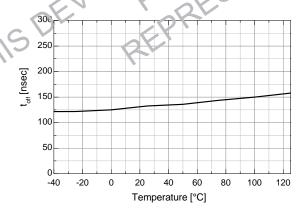
Figure 8. in-on ising Time vs. Temperature





rure). Turn-off Failing Time vs. Temperature

Figure 20. Turn-on Delay Time vs. Temperature



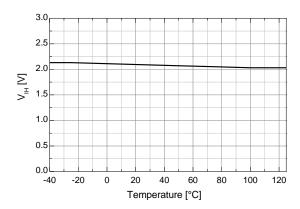
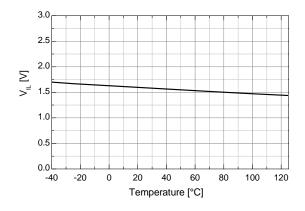


Figure 21. Turn-off Delay Time vs. Temperature

Figure 22. Logic Input High Voltage vs. Temperature



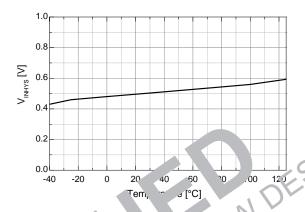
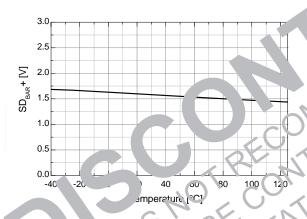
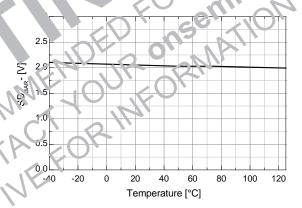


Figure 23. Logic Input Low Voltage vs. Temperature

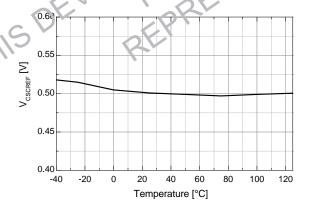
Figure . Le 'c Inp Hysteres's vs. Temperature





Fure 2 . SD Positive Threshold vs. Ten perature

Figure 26. SD Negative Threshold vs. Temperature



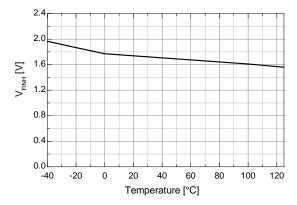
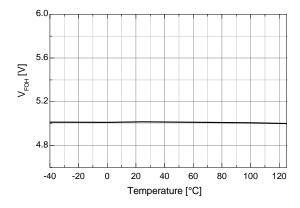


Figure 27. V_{CSCREF} vs. Temperature

Figure 28. Fault Input High Voltage vs. Temperature



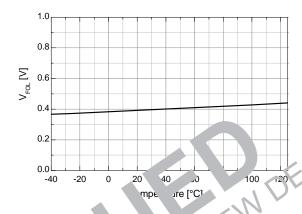
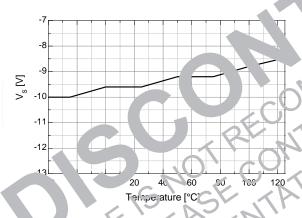


Figure 29. Fault Output High Voltage vs. Temperature

Figure 30. 'aul. 'utr' Low Voltage vs. Temperature



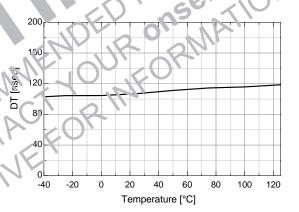


Figure 31. Allowable Mediative V_S Voltage for Signal Propagation to High Side vs. Temperature

Figure 32. Dead Time vs. Temperature

Switching Time Definitions

The overall switching timing waveforms definition of FAN7384 as shown Figure 33.

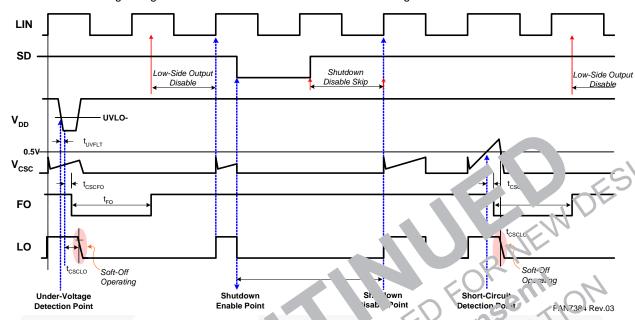


Figure 33. Timing Way of orus Definition

Typical Application Information

1. Protection Function

1.1 Under-Voltage Lockout (UVLO)

The high- and low-side drivers include under-voltage lockout (UVLO) protection circuitry that monitors the supply voltage (V_{DD}) and bootstrap capacitor voltage (V_{BS}) independently. It can be designed to prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage. Moreover, the UVLO hysteresis prevents chattering during power supply transitions. If the supply voltage (V_{DD}) maintains an under-voltage condition over under-voltage filtering times (typically 16 μ s), the fault and soft-off circuits are activated, as shown Figure 34.

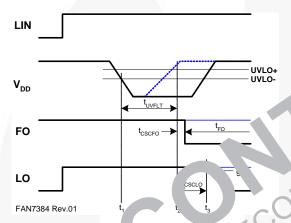


Figure 34. Waveform for Un er-Voltage Lockout

1.2 Shoot Prough Prention Function

T' FA. '38 has a shoot-through prevention circuitry to the moning shapping and low-side inputs. It can be declined prevent outputs of high and low-side turning on at the time, as shown Figure 35 and 26.

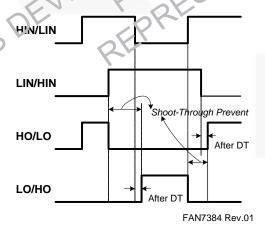


Figure 35. Waveforms for Shoot-Through Prevention

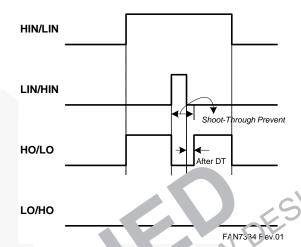


Figure 36. W reform for loot-Through Prevention

3 c s. nt Protection Function

The FA 7384 has o er-current detection circuitry that moreovers the current-by-current sensing resistor connected from the low-side switch sour ∞ (V_{SL}) to ground.

It is a built in time-filer from the over-current event to prevent malfunction from a noise source, such as leading edge pilse in inductive load application, as shown Figure 37.

The sensing current is calculated as follows:

$$I_{\rm CS} = \frac{V_{\rm CSCREF}}{R_{\rm CS}} [A] \tag{1}$$

where,

V_{CSCREF}: Reference voltage of current sense comparator

R_{CS}: Current sensing resistor

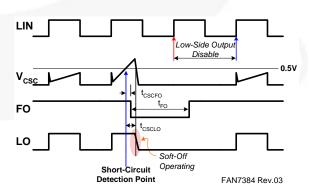


Figure 37. Waveforms for Short-Circuit Protection

2. Layout Considerations

For optimum performance, considerations must be taken during printed circuit board (PCB) layout.

2.1 Supply Capacitors

If the output stages are able to quickly turn on a switching device with a high value of current, the supply capacitors must be placed as close as possible to the device pins (V_{DD} and GND for the ground-tied supply, V_{B} and V_{S} for the floating supply) to minimize parasitic inductance and resistance.

2.2 Gate-Drive Loop

Current loops behave like antennae, able to receive and transmit noise. To reduce the noise coupling/emission and improve the power switch turn-on and off performance, gate-drive loops must be reduced as much as possible.

2.3 Ground Plane

To minimize noise coupling, the ground plane should not be placed under or near the high-voltage floating side.

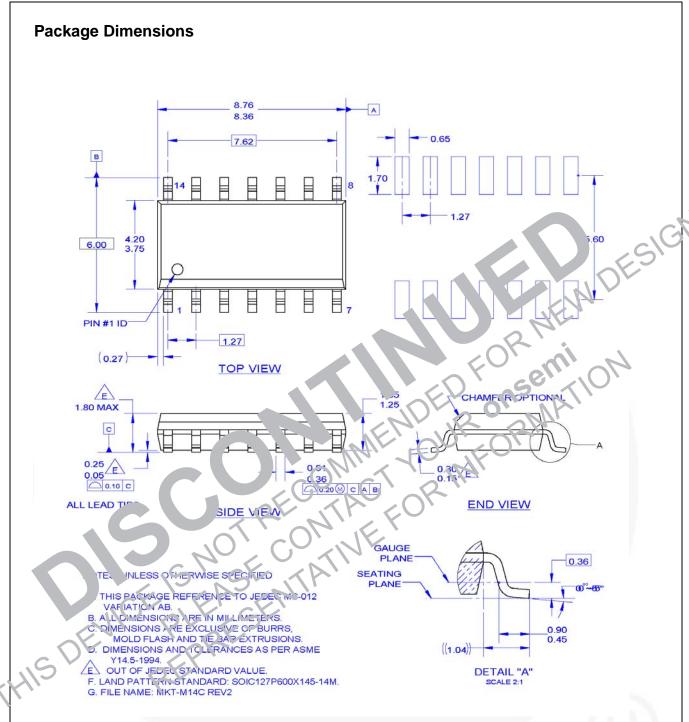


Figure 38. 14-Lead, Small Outline Integrated Circuit (SOIC), Non-JEDEC, .150 Inch Narrow Body, 225SOP

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